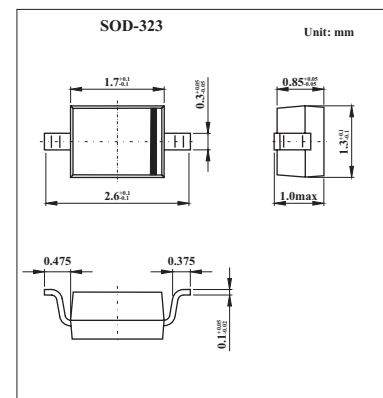


## Silicon Schottky Diode

## BAT68-03W

## ■ Features

- For mixer applications in the VHF/UHF range
- For high speed switching

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	8	V
Forward current	$I_F$	130	mA
Total Power dissipation $T_S = 95^\circ\text{C}$	$P_{tot}$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Operating temperature range	$T_{op}$	-65 to +150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Junction ambient	$R_{thJA}$	445	K/W
Junction - soldering point	$R_{thJS}$	365	K/W

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	$V_{(BR)}$	$I_{(BR)} = 10 \mu\text{A}$	8			V
Reverse current	$I_R$	$V_R = 1 \text{ V}, T_A = 25^\circ\text{C}$			0.1	$\mu\text{A}$
		$V_R = 1 \text{ V}, T_A = 60^\circ\text{C}$			1.2	
Forward voltage	$V_F$	$I_F = 1 \text{ mA}$		318	340	mV
		$I_F = 10 \text{ mA}$	340	390	500	
Diode capacitance	$C_T$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			1	pF
Differential forward resistance	$R_F$	$I_F = 5 \text{ mA}$			10	$\Omega$

Forward current  $I_F = f(T_A^*; T_S)$

\*) : mounted on alumina 15mm x 16.7mm x 0.7mm

## ■ Marking

Marking	K
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